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Kind regards,

Team Nexperia

Schottky barrier diodes in small packages Rev. 06 — 21 December 2006

**Product data sheet** 

### 1. Product profile

### 1.1 General description

Planar Schottky barrier diodes with an integrated guard ring for stress protection. Encapsulated in small Surface-Mounted Device (SMD) plastic packages.

#### Table 1.Product overview

Type number	Package		Configuration
	NXP	JEITA	
1PS76SB21	SOD323	SC-76	single
BAT721	SOT23	-	single
BAT721A	SOT23	-	dual common anode
BAT721C	SOT23	-	dual common cathode
BAT721S	SOT23	-	dual series

### 1.2 Features

- Low forward voltage
- Small SMD plastic packages
- Low capacitance

#### **1.3 Applications**

- Ultra high-speed switching
- Voltage clamping
- Line termination
- Reverse polarity protection

### 1.4 Quick reference data

Table 2.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode	)					
l <sub>F</sub>	forward current		-	-	200	mA
V <sub>R</sub>	reverse voltage		-	-	40	V
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 200 mA	<u>[1]</u> _	-	550	mV



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## 2. Pinning information

Pin	Description	Simplified outline	Symbol
1PS76SB2	21		
1	cathode	[1]	
2	anode		1 <u>-</u> 2 sym001
BAT721			
1	anode		
2	not connected	3	3
3	cathode	1 2 006aaa144	1 2 n.c. 006aaa436
BAT721A			
1	cathode (diode 1)		
2	cathode (diode 2)	3	3
3	anode (diode 1), anode (diode 2)	1 2 006aaa144	1 2 006aaa439
BAT721C			
1	anode (diode 1)	_	
2	anode (diode 2)	3	3
3	cathode (diode 1), cathode (diode 2)	1 2 006aaa144	1 - JC - 2 006aaa438
BAT721S			
1	anode (diode 1)	_	
2	cathode (diode 2)	3	3
3	cathode (diode 1), anode (diode 2)	12	1 2 006aaa437

[1] The marking bar indicates the cathode.

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### 3. Ordering information

Table 4. Orde	ering inform	ation				
Type number	Package	Package				
	Name	Description	Version			
1PS76SB21	SC-76	plastic surface-mounted package; 2 leads	SOD323			
BAT721	-	plastic surface-mounted package; 3 leads	SOT23			
BAT721A						
BAT721C						
BAT721S						

### 4. Marking

Table 5.   Marking codes	
Type number	Marking code <sup>[1]</sup>
1PS76SB21	S1
BAT721	L7*
BAT721A	L8*
BAT721C	L9*
BAT721S	L0*

[1] \* = -: made in Hong Kong

\* = p: made in Hong Kong

- \* = t: made in Malaysia
- \* = W: made in China

### 5. Limiting values

#### Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		0 7 (	,		
Symbol	Parameter	Conditions	Min	Max	Unit
Per diode					
V <sub>R</sub>	reverse voltage		-	40	V
I <sub>F</sub>	forward current		-	200	mA
I <sub>FSM</sub>	non-repetitive peak forward current	half sine wave; JEDEC method; t <sub>p</sub> = 8.3 ms	-	1	A
Tj	junction temperature		-	125	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

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#### **Thermal characteristics** 6.

Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode	)					
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
	1PS76SB21		-	-	450	K/W
	BAT721		-	-	500	K/W
	BAT721A		-	-	500	K/W
	BAT721C		-	-	500	K/W
	BAT721S		-	-	500	K/W

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

#### **Characteristics** 7.

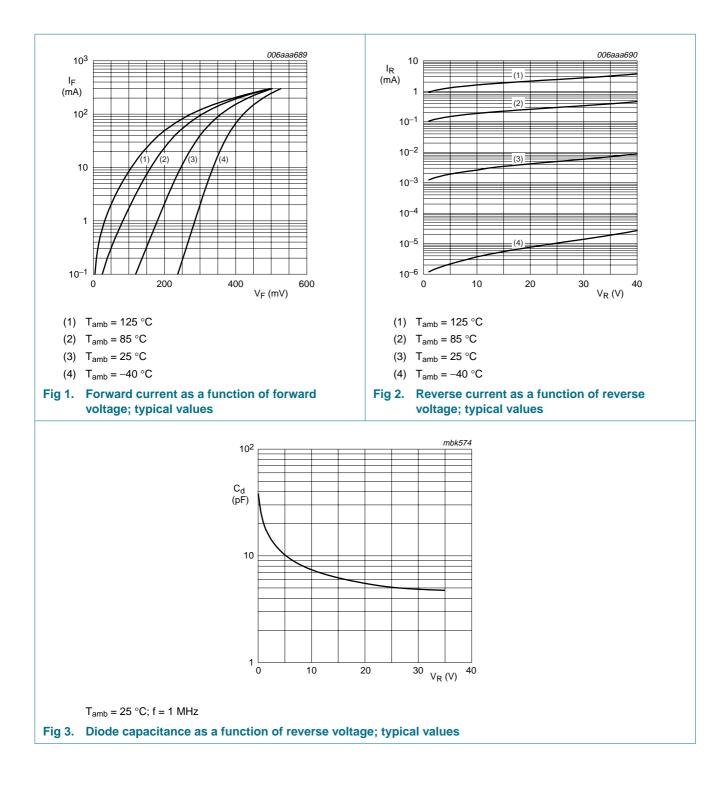
<b>Table 8.</b> <i>T<sub>amb</sub> = 25</i>	Characteristics °C unless otherwise s	specified.				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode	)					
V <sub>F</sub> forward voltage	forward voltage	I <sub>F</sub> = 10 mA	<u>[1]</u> -	-	300	mV
		I <sub>F</sub> = 100 mA	<u>[1]</u> -	-	420	mV
		I <sub>F</sub> = 200 mA	<u>[1]</u> -	-	550	mV
I <sub>R</sub>	reverse current	V <sub>R</sub> = 30 V	-	-	15	μΑ
		$V_R = 30 \text{ V}; \text{ T}_j = 100 ^{\circ}\text{C}$	-	-	3	mA
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 0 V; f = 1 MHz	-	40	50	pF
						-

1PS76SB21\_BAT721\_SER\_6

### **NXP Semiconductors**

# 1PS76SB21; BAT721 series

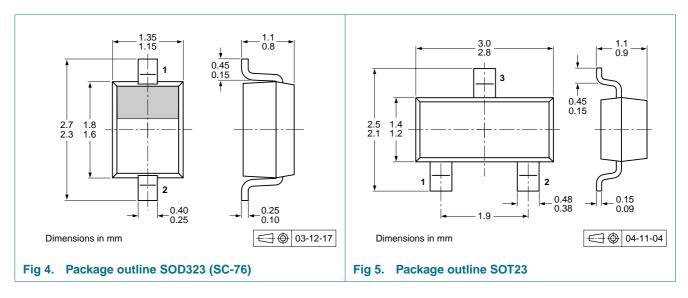
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### 8. Package outline



### 9. Packing information

#### Table 9. Packing methods

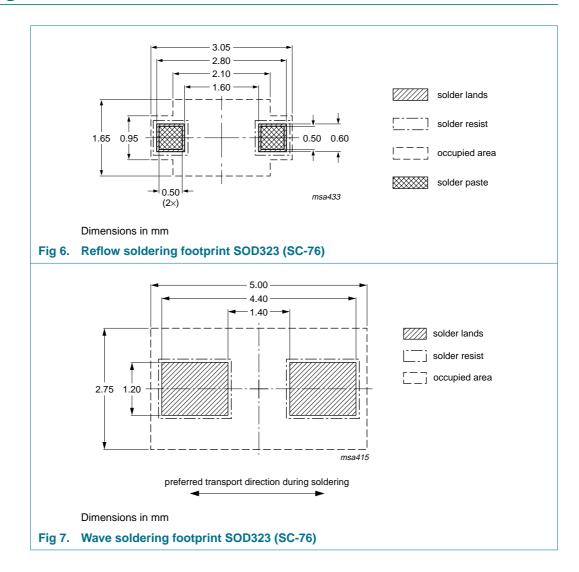
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description		Packing quantity		
			3000	10000		
1PS76SB21	SOD323	4 mm pitch, 8 mm tape and reel	-115	-135		
BAT721	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235		
BAT721A						
BAT721C						
BAT721S						

[1] For further information and the availability of packing methods, see Section 13.

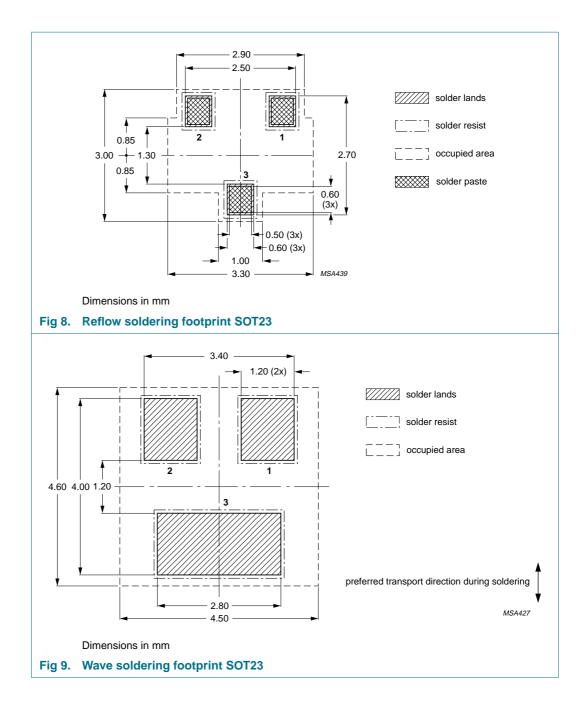
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### **10. Soldering**



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### 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
1PS76SB21_BAT721_SER_0	6 20061221	Product data sheet	-	1PS76SB21_BAT721 _SER_5		
Modifications:	Amended T	able 10 "Revision history"				
1PS76SB21_BAT721_SER_	5 20061205	Product data sheet	-	BAT721_SERIES_4 1PS76SB21_3		
Modifications:		of this data sheet has bee of NXP Semiconductors.	n redesigned to comply	y with the new identity		
	<ul> <li>Legal texts</li> </ul>	have been adapted to the	new company name w	here appropriate.		
	<ul> <li>This data sl 1PS76SB2</li> </ul>	heet is a combination of da 1_3.	ata sheets BAT721_SE	RIES_4 and		
	• Table 1 "Pro	oduct overview": added				
	<ul> <li>Section 1.2</li> </ul>	"Features": amended				
	<ul> <li>Section 1.3</li> </ul>	"Applications": amended				
	<ul> <li>Table 2 "Qu</li> </ul>	lick reference data": added	ł			
	<ul> <li>Table 5 "Ma</li> </ul>	<ul> <li><u>Table 5 "Marking codes"</u>: for 1PS76SB21 amended</li> </ul>				
	<ul> <li><u>Table 5 "Marking codes"</u>: enhanced table note section</li> </ul>					
	Table 6 "Lin	<ul> <li><u>Table 6 "Limiting values"</u>: indication per diode added</li> </ul>				
	Table 6 "Lin	<ul> <li><u>Table 6 "Limiting values</u>": for 1PS76SB21 I<sub>FSM</sub> condition amended</li> </ul>				
	Table 6 "Lin	<ul> <li><u>Table 6 "Limiting values"</u>: T<sub>amb</sub> ambient temperature added</li> </ul>				
	Table 7 "Th	<ul> <li><u>Table 7 "Thermal characteristics"</u>: indication per diode added</li> </ul>				
	<ul> <li><u>Table 7</u>: R<sub>th</sub></li> </ul>	<ul> <li><u>Table 7</u>: R<sub>th(j-a)</sub> thermal resistance from junction to ambient condition amended</li> </ul>				
		<ul> <li><u>Table 8 "Characteristics"</u>: indication per diode added</li> </ul>				
	<u>Table 8 "Characteristics"</u> : reference to <u>Table note 1</u> amended					
		1PS76SB21 C <sub>d</sub> minimum	value changed to typic	al value		
		id <u>2</u> : amended				
		d 5: superseded by minimi				
		Packing information": adde	d			
		"Soldering": added				
	Section 12	"Legal information": update	ed			
BAT721_SERIES_4	20040315	Product specification	-	BAT721_SERIES_3		
1PS76SB21_3	20040126	Product specification	-	1PS76SB21_2		

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### 12. Legal information

#### **12.1 Data sheet status**

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Date of release: 21 December 2006 Document identifier: 1PS76SB21\_BAT721\_SER\_6



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